

PSMN3R0-30YL

N-channel TrenchMOS logic level FET

Rev. 03 — 28 December 2009

Product data sheet

1. Product profile

1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in industrial and communications applications.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for logic level gate drive sources

1.3 Applications

- Class-D amplifiers
- DC-to-DC converters
- Motor control
- Server power supplies

1.4 Quick reference data

Table 1. Quick reference

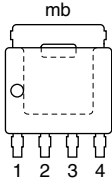
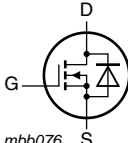
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25\text{ °C}; T_j \leq 175\text{ °C}$	-	-	30	V
I_D	drain current	$T_{mb} = 25\text{ °C}; V_{GS} = 10\text{ V};$ see Figure 1	[1]	-	100	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C};$ see Figure 2	-	-	81	W
Dynamic characteristics						
Q_{GD}	gate-drain charge	$V_{GS} = 4.5\text{ V}; I_D = 10\text{ A};$ $V_{DS} = 12\text{ V};$ see Figure 14 and 15	-	5.1	-	nC
$Q_{G(tot)}$	total gate charge	$V_{GS} = 4.5\text{ V}; I_D = 10\text{ A};$ $V_{DS} = 12\text{ V};$ see Figure 14	-	21	-	nC
Static characteristics						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}; I_D = 15\text{ A};$ $T_j = 25\text{ °C}$	-	2.19	3	m Ω

[1] Continuous current is limited by package.



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		
2	S	source		
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain		

SOT669 (LFAK)

3. Ordering information

Table 3. Ordering information

Type number	Package		Version
	Name	Description	
PSMN3R0-30YL	LFAK	plastic single-ended surface-mounted package (LFAK); 4 leads	SOT669

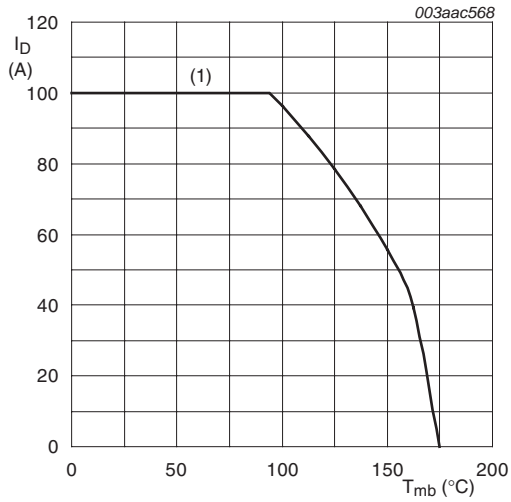
4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

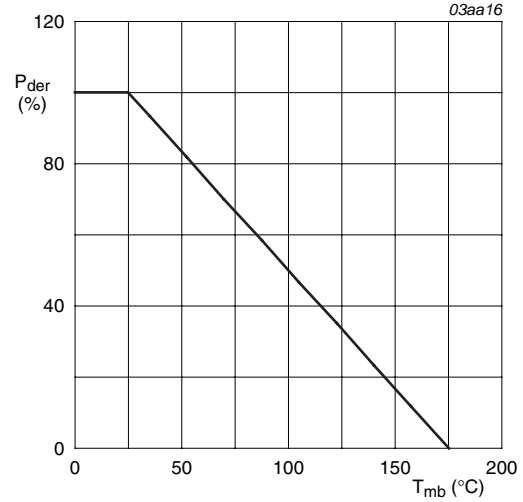
Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25\text{ °C}$; $T_j \leq 175\text{ °C}$	-	30	V
V_{DGR}	drain-gate voltage	$T_j \geq 25\text{ °C}$; $T_j \leq 175\text{ °C}$; $R_{GS} = 20\text{ k}\Omega$	-	30	V
V_{GS}	gate-source voltage		-20	20	V
I_D	drain current	$V_{GS} = 10\text{ V}$; $T_{mb} = 100\text{ °C}$; see Figure 1	[1]	96	A
		$V_{GS} = 10\text{ V}$; $T_{mb} = 25\text{ °C}$; see Figure 1	[1]	100	A
I_{DM}	peak drain current	$t_p \leq 10\text{ }\mu\text{s}$; pulsed; $T_{mb} = 25\text{ °C}$; see Figure 3	-	497	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C}$; see Figure 2	-	81	W
T_{stg}	storage temperature		-55	175	°C
T_j	junction temperature		-55	175	°C
Source-drain diode					
I_S	source current	$T_{mb} = 25\text{ °C}$;	[1]	100	A
I_{SM}	peak source current	$t_p \leq 10\text{ }\mu\text{s}$; pulsed; $T_{mb} = 25\text{ °C}$	-	497	A
Avalanche ruggedness					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10\text{ V}$; $T_{j(\text{init})} = 25\text{ °C}$; $I_D = 100\text{ A}$; $V_{sup} \leq 30\text{ V}$; $R_{GS} = 50\text{ }\Omega$; unclamped	-	75	mJ

[1] Continuous current is limited by package.



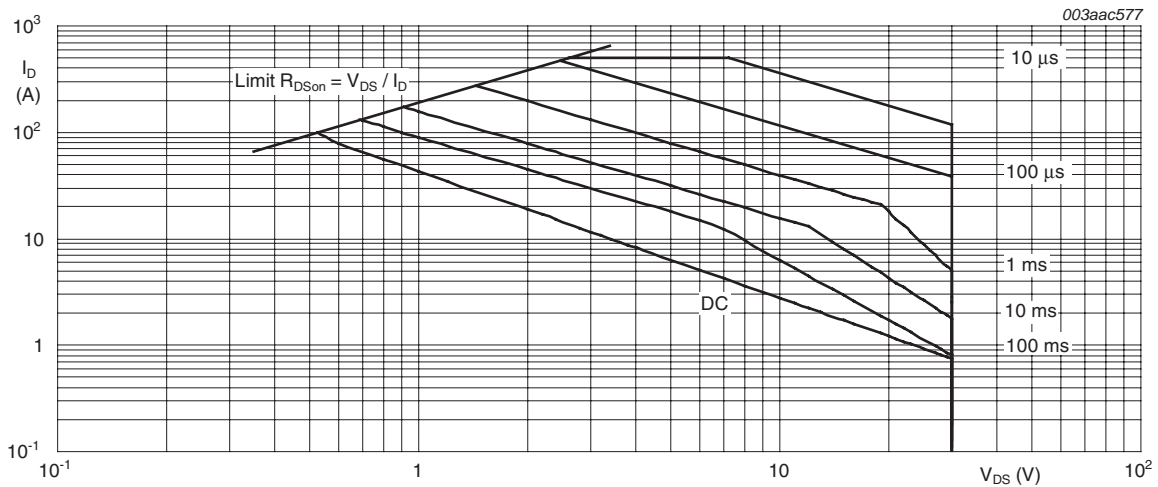
$V_{GS} \geq 10\text{ V}$; (1) Capped at 100 A due to package

Fig 1. Continuous drain current as a function of mounting base temperature



$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}\text{C})}} \times 100\%$$

Fig 2. Normalized total power dissipation as a function of mounting base temperature



$T_{mb} = 25^{\circ}\text{C}$; I_{DM} is single pulse
(1) Capped at 100 A due to package.

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	0.9	1.5	K/W

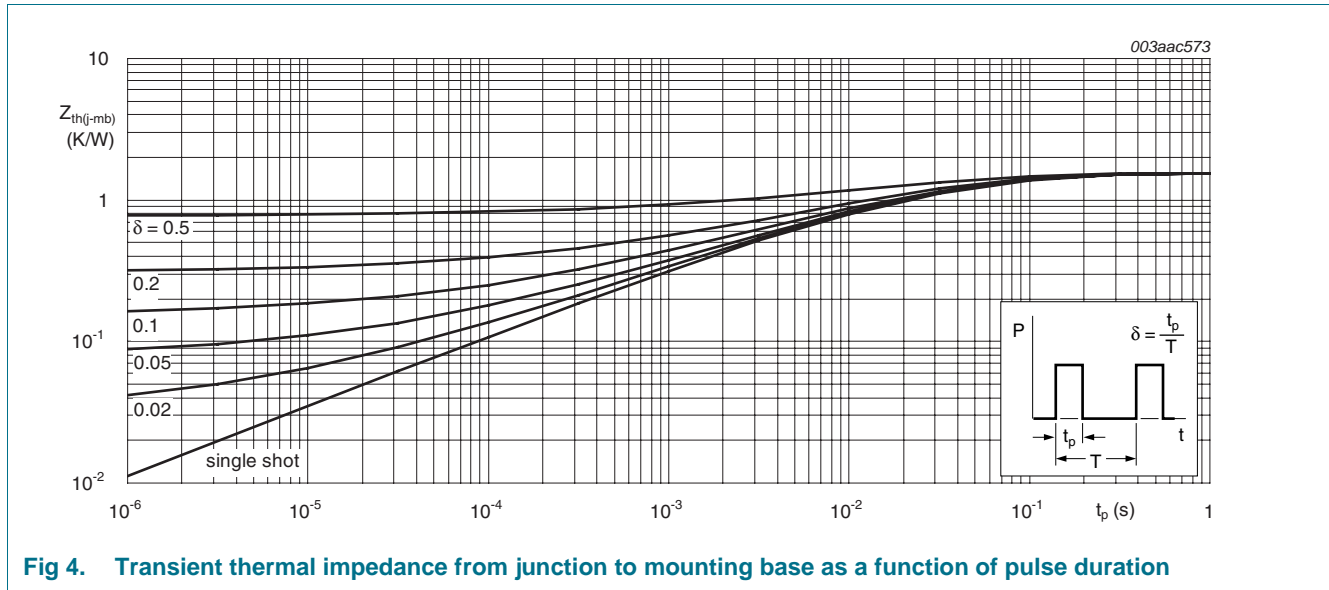


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 20\text{ A}; V_{GS} = 0\text{ V}; T_j = 25\text{ }^\circ\text{C}; t_{av} = 100\text{ ns}$	35	-	-	V
		$I_D = 250\text{ }\mu\text{A}; V_{GS} = 0\text{ V}; T_j = 25\text{ }^\circ\text{C}$	30	-	-	V
		$I_D = 250\text{ }\mu\text{A}; V_{GS} = 0\text{ V}; T_j = -55\text{ }^\circ\text{C}$	27	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1\text{ mA}; V_{DS} = V_{GS}; T_j = 25\text{ }^\circ\text{C}$; see Figure 11 and 12	1.3	1.7	2.15	V
		$I_D = 1\text{ mA}; V_{DS} = V_{GS}; T_j = 150\text{ }^\circ\text{C}$; see Figure 12	0.65	-	-	V
		$I_D = 1\text{ mA}; V_{DS} = V_{GS}; T_j = -55\text{ }^\circ\text{C}$; see Figure 12	-	-	2.45	V
I_{DSS}	drain leakage current	$V_{DS} = 30\text{ V}; V_{GS} = 0\text{ V}; T_j = 25\text{ }^\circ\text{C}$	-	-	1	μA
		$V_{DS} = 30\text{ V}; V_{GS} = 0\text{ V}; T_j = 150\text{ }^\circ\text{C}$	-	-	100	μA
I_{GSS}	gate leakage current	$V_{GS} = 16\text{ V}; V_{DS} = 0\text{ V}; T_j = 25\text{ }^\circ\text{C}$	-	-	100	nA
		$V_{GS} = -16\text{ V}; V_{DS} = 0\text{ V}; T_j = 25\text{ }^\circ\text{C}$	-	-	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 4.5\text{ V}; I_D = 15\text{ A}; T_j = 25\text{ }^\circ\text{C}$	-	3.04	4.04	m Ω
		$V_{GS} = 10\text{ V}; I_D = 15\text{ A}; T_j = 150\text{ }^\circ\text{C}$; see Figure 13	-	-	5.2	m Ω
		$V_{GS} = 10\text{ V}; I_D = 15\text{ A}; T_j = 25\text{ }^\circ\text{C}$	-	2.19	3	m Ω
R_G	gate resistance	$f = 1\text{ MHz}$	-	0.55	1.5	Ω
Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	$I_D = 10\text{ A}; V_{DS} = 12\text{ V}; V_{GS} = 10\text{ V}$; see Figure 14 and 15	-	45.8	-	nC
		$I_D = 0\text{ A}; V_{DS} = 0\text{ V}; V_{GS} = 10\text{ V}$	-	43	-	nC
		$I_D = 10\text{ A}; V_{DS} = 12\text{ V}; V_{GS} = 4.5\text{ V}$; see Figure 14	-	21	-	nC
Q_{GS}	gate-source charge	$I_D = 10\text{ A}; V_{DS} = 12\text{ V}; V_{GS} = 4.5\text{ V}$; see Figure 14 and 15	-	7.02	-	nC
$Q_{GS(th)}$	pre-threshold gate-source charge		-	4.74	-	nC
$Q_{GS(th-pl)}$	post-threshold gate-source charge		-	2.28	-	nC
Q_{GD}	gate-drain charge		-	5.1	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	$V_{DS} = 12\text{ V}$; see Figure 14 and 15	-	2.37	-	V
C_{iss}	input capacitance	$V_{DS} = 12\text{ V}; V_{GS} = 0\text{ V}; f = 1\text{ MHz}; T_j = 25\text{ }^\circ\text{C}$; see Figure 16	-	2822	-	pF
C_{oss}	output capacitance		-	615	-	pF
C_{rss}	reverse transfer capacitance		-	260	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 12\text{ V}; R_L = 0.5\text{ }\Omega; V_{GS} = 4.5\text{ V}$; $R_{G(ext)} = 4.7\text{ }\Omega$	-	34	-	ns
t_r	rise time		-	58	-	ns
$t_{d(off)}$	turn-off delay time		-	50	-	ns
t_f	fall time		-	21	-	ns

Table 6. Characteristics ...continued

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Source-drain diode						
V_{SD}	source-drain voltage	$I_S = 25\text{ A}$; $V_{GS} = 0\text{ V}$; $T_j = 25\text{ }^\circ\text{C}$; see Figure 17	-	0.82	1.2	V
t_{rr}	reverse recovery time	$I_S = 20\text{ A}$; $di_S/dt = -100\text{ A}/\mu\text{s}$; $V_{GS} = 0\text{ V}$;	-	35	-	ns
Q_r	recovered charge	$V_{DS} = 20\text{ V}$	-	29	-	nC

[1] Tested to JEDEC standards where applicable.

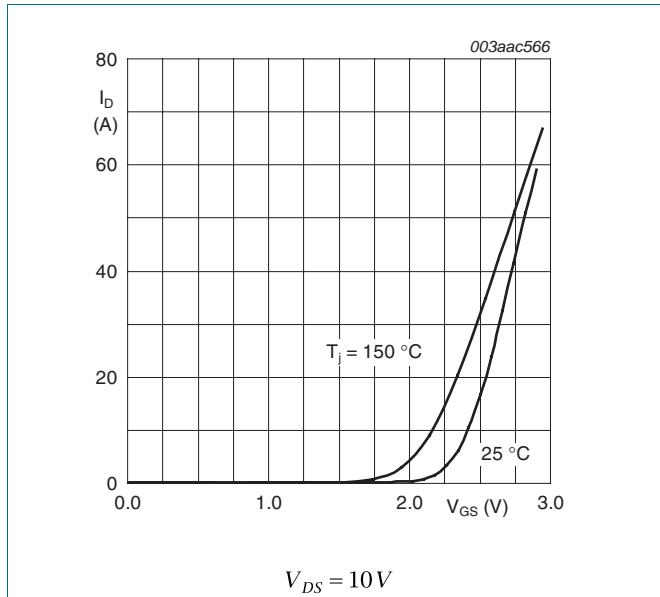


Fig 5. Transfer characteristics: drain current as a function of gate-source voltage; typical values

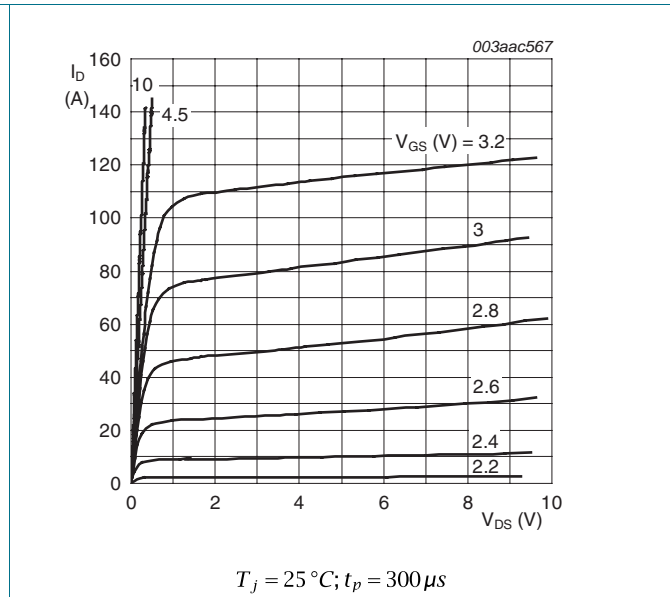


Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values

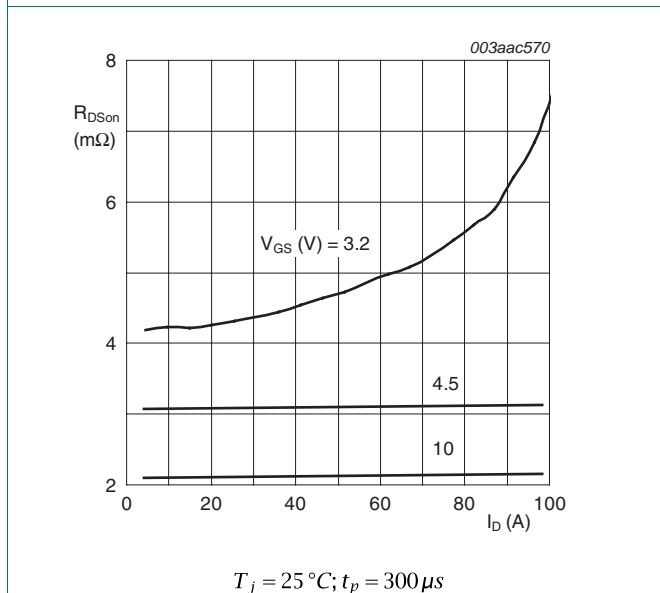


Fig 7. Drain-source on-state resistance as a function of drain current; typical values

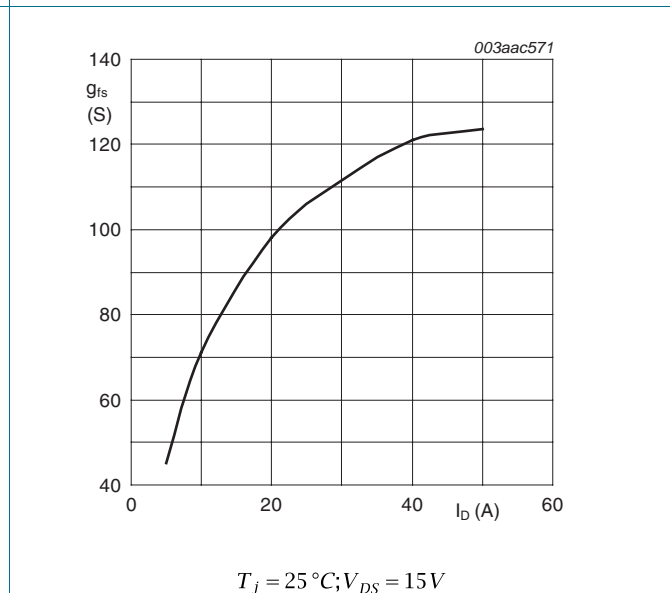
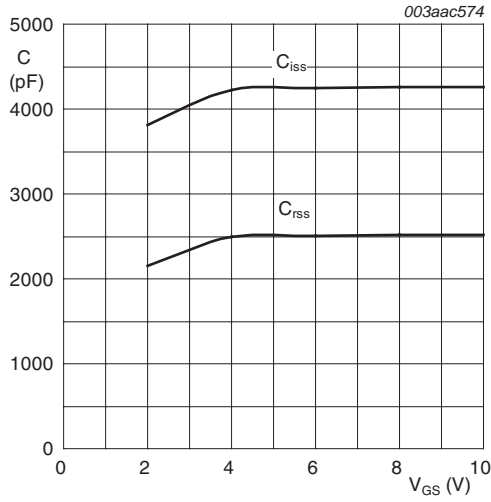
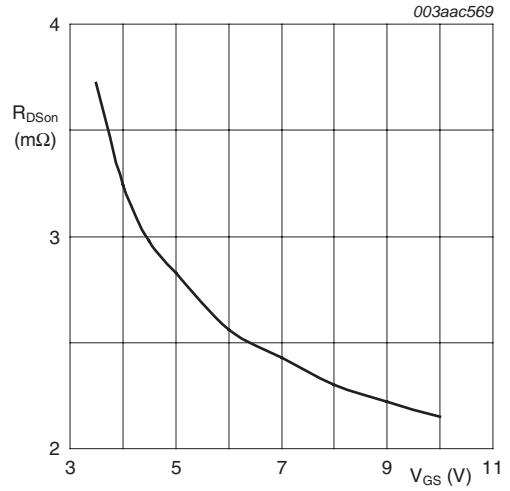


Fig 8. Forward transconductance as a function of drain current; typical values



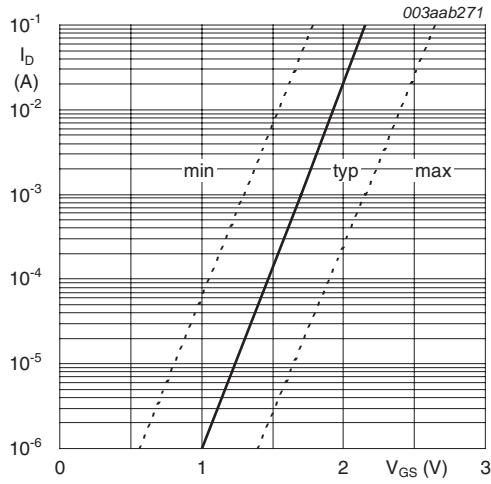
$V_{DS} = 0V; f = 1MHz$

Fig 9. Input and reverse transfer capacitances as a function of gate-source voltage; typical values



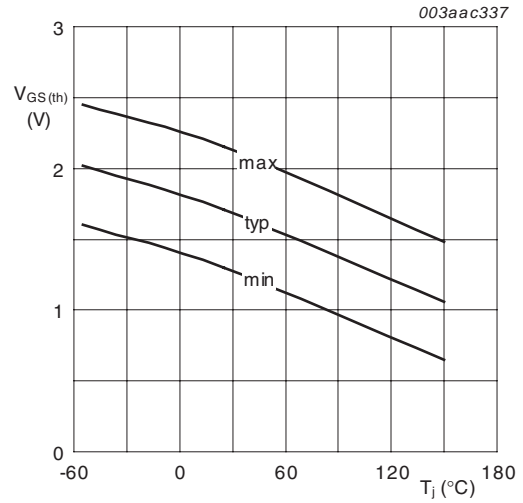
$T_j = 25^\circ C; I_D = 10A$

Fig 10. Drain-source on-state resistance as a function of gate-source voltage; typical values



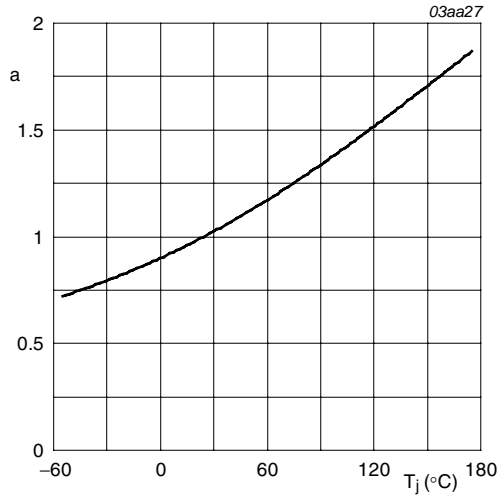
$T_j = 25^\circ C; V_{DS} = 5V$

Fig 11. Sub-threshold drain current as a function of gate-source voltage



$I_D = 1mA; V_{DS} = V_{GS}$

Fig 12. Gate-source threshold voltage as a function of junction temperature



$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature

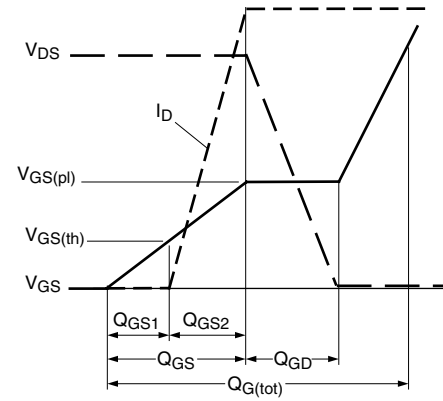
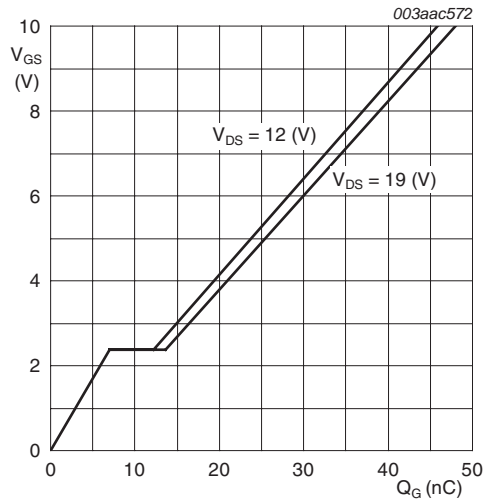
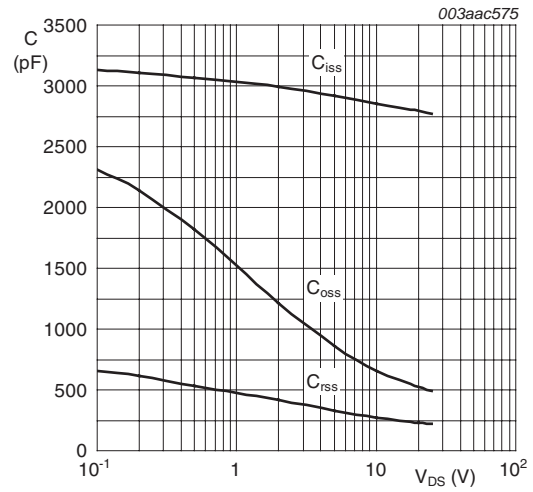


Fig 14. Gate charge waveform definitions



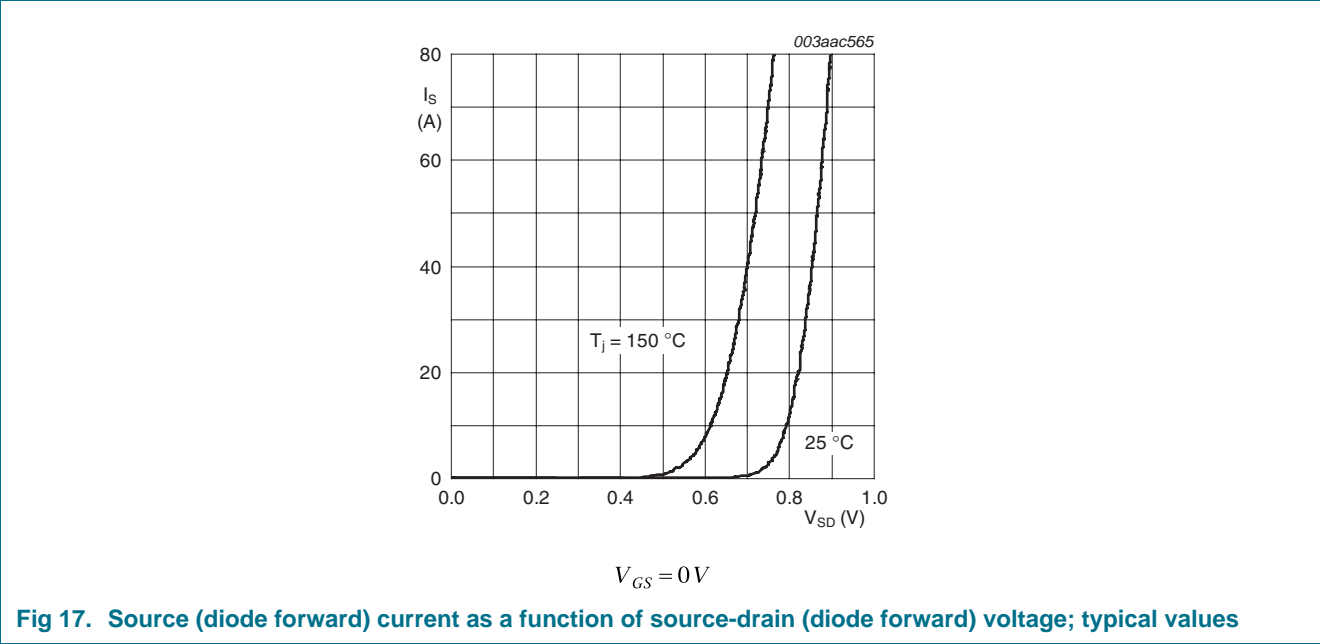
$T_j = 25^{\circ}C; I_D = 10A$

Fig 15. Gate-source voltage as a function of gate charge; typical values



$V_{GS} = 0V; f = 1MHz$

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



7. Package outline

Plastic single-ended surface-mounted package (LFPAK); 4 leads

SOT669

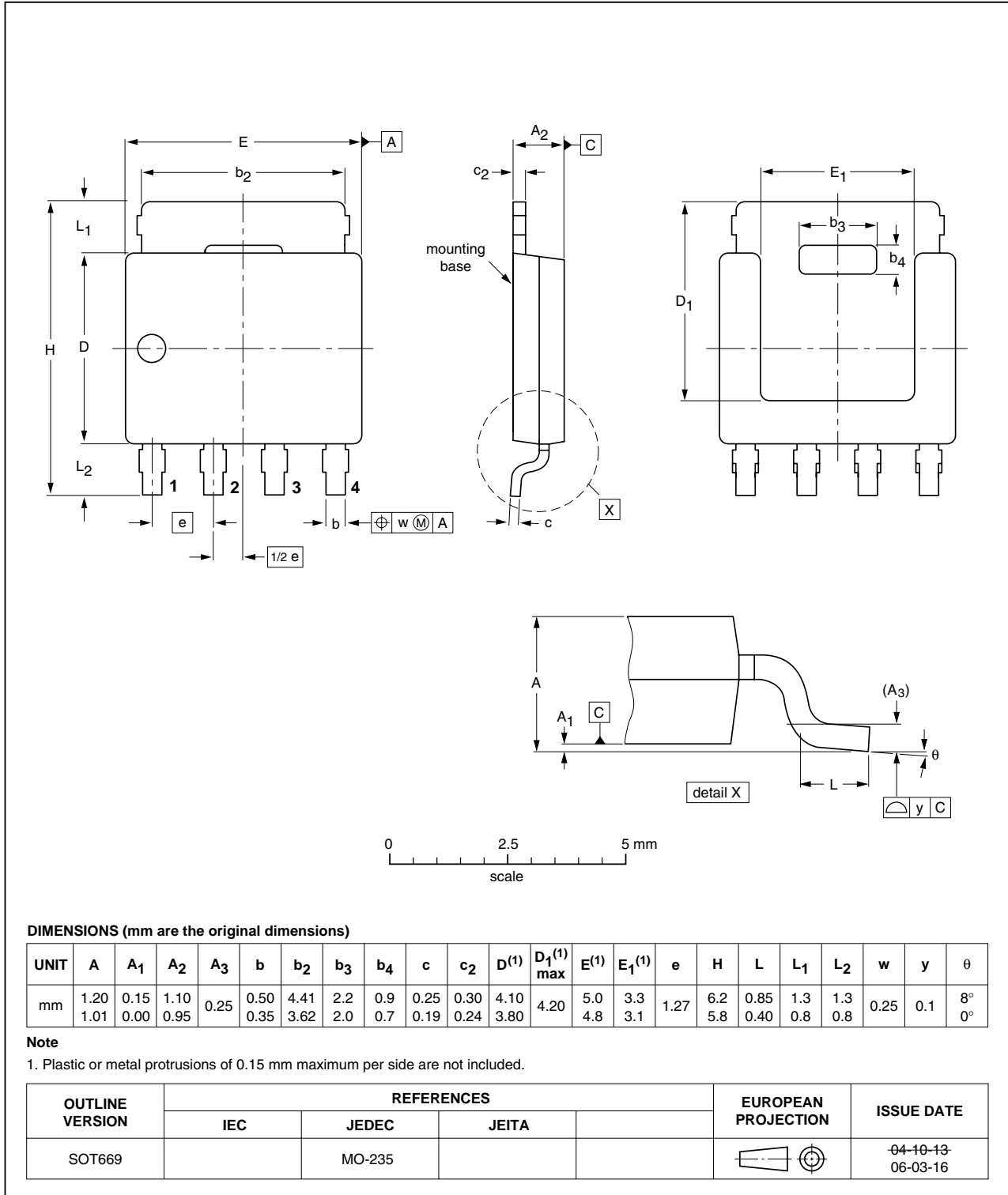


Fig 18. Package outline SOT669 (LFPAK)

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN3R0-30YL_3	20091228	Product data sheet	-	PSMN3R0-30YL_2
Modifications:	• Various changes to content.			
PSMN3R0-30YL_2	20090105	Product data sheet	-	PSMN3R0-30YL_1
PSMN3R0-30YL_1	20080909	Preliminary data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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Date of release: 28 December 2009

Document identifier: PSMN3R0-30YL_3